אוניברסיטת בן-גוריון בנגב
Ben-Gurion University of the Negev

Nano-Fabrication Center

Reactive-ion etching

Description

Reactive-ion etching (RIE) is an etching technology used in micro fabrication for dry etching of structures. RIE uses chemically reactive plasma to remove materials from surface.

Specifications / Capabilities

Our Corial 200 RIE system with vacuum uses reactive gases for etching of III-V and II-VI compounds like GaAs, GaAlAs, InP, InGaAsP, ZnS, CdTe and HgCdTe.
The reactor designed to achieve etching for up to 200 mm wafer size.
Low Anode / Cathode area ratio to achieve excellent etch uniformities on large areas and minimize etch damages.
Wafer clamping with helium cooling on back side to work at high RF power with no photoresist damage
Wide range of working pressure (1 to 400 mT).

Standard tolerance: 10-15%

Available Gases

Plasma of gases**:** CHF3, SF6, Ar,O2

Etching materials: Photoresist, SiO2, Polyimide, and Si3N4.

Link

http://www.corial.net/

http://www.corial.net/index.php?option=com_content&view=article&id=75&Itemid=178